

Claims 1-36 and 39-42 are cancelled; claims 43-45 are added; claims 37-38 and 43-45 are pending in the application. Applicant requests examination of the pending claims.

The added claims 43-45 are fully supported by the specification. With respect to claim 43, support for the claimed subject matter is found in the specification at page 9, lines 13-15. With respect to claim 44, the subject matter claimed is supported by the specification at page 11, lines 3-7. With respect to claim 45, the subject matter claimed is supported by the specification at page 13, lines 11-13.

Respectfully submitted,

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Priority Group Art Unit 2813
Priority Examiner Schillinger, L.
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Title: Methods of Forming a Thin Film Transistor

VERSION WITH MARKINGS TO SHOW CHANGES MADE ACCOMPANYING
PRELIMINARY AMENDMENT

In the Specification

The replacement specification paragraphs incorporate the following amendments. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

At p. 1, before the "Technical Field" Section, insert

RELATED PATENT DATA

This patent is a divisional application of U.S. Patent Application Serial No. 09/837,645 which was filed on April 17, 2001, which is a continuation of U.S. Patent No. 6,238,957, issued on May 29, 2001, which is a continuation of U.S. Patent No. 6,001,675, issued on December 14, 1999, which is a continuation of U.S. Patent No. 5,665,611, which was issued on September 9, 1997.

In the Claims

The claims have been amended as follows. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

Claims 1-36 and 39-42 are cancelled.

The following claims are added:

43. (New) The method of claim 37 wherein the forming a fluorine containing layer comprises forming a sacrificial fluorine containing layer over the thin film transistor layer by chemical vapor deposition utilizing WF₆ and SiH₄ precursors.

44. (New) The method of claim 43 further comprising after the transferring fluorine, removing the sacrificial layer from over the thin film transistor layer.

45. (New) A method of forming a bottom-gated thin film transistor comprising the following steps:

forming a transistor gate;

forming a polycrystalline thin film transistor layer over the transistor gate;

forming a fluorine containing layer over the polycrystalline thin film transistor layer;

providing a buffering layer intermediate the thin film transistor layer and the fluorine containing layer; and

transferring fluorine into the polycrystalline thin film transistor layer from the fluorine containing layer.

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